



A Product Line of Diodes Incorporated



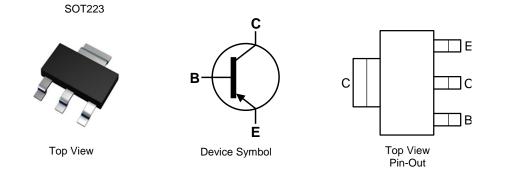
500V PNP HIGH VOLTAGE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -500V
- I_C = -150mA High Continuous Current
- I_{CM} = -500mA Peak Pulse Current
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (@3)
- Weight: 0.112 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT560TA	AEC-Q101	FZT560	7	12	1,000
FZT560QTA	Automotive	FZT560	7	12	1,000
FZT560TC	AEC-Q101	FZT560	13	12	4,000
FZT560QTC	Automotive	FZT560	13	12	4,000

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

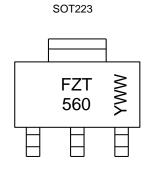
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 560 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-500	V
Collector-Emitter Voltage	V _{CEO}	-500	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-150	mA
Peak Pulse Current	ICM	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	Р	2	W
	(Note 7)	PD	3	W
Thermal Decistorian Investion to Ambient	(Note 6)	P	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	41.7	°C/W
Thermal Resistance, Junction to Leads	(Note 8)	R _{θJL}	14.8	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

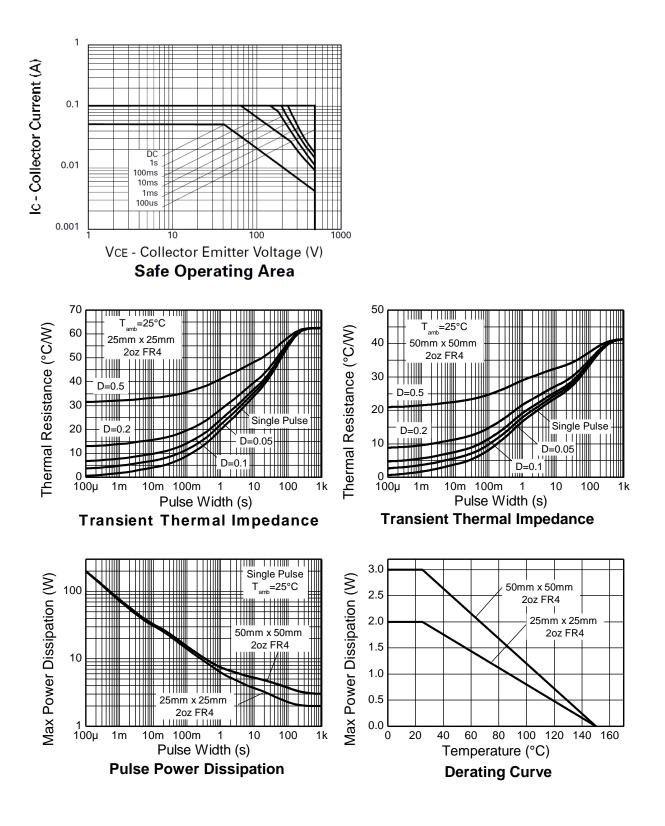
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air To a device mounted with the collector lead on 2011 x 201111 x 20111 x 201111 x 2011111 x 201111 x 2011111 x 201111111 x 2011111 x 2011111 x 201111 x 2011111





Thermal Characteristics and Derating Information







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

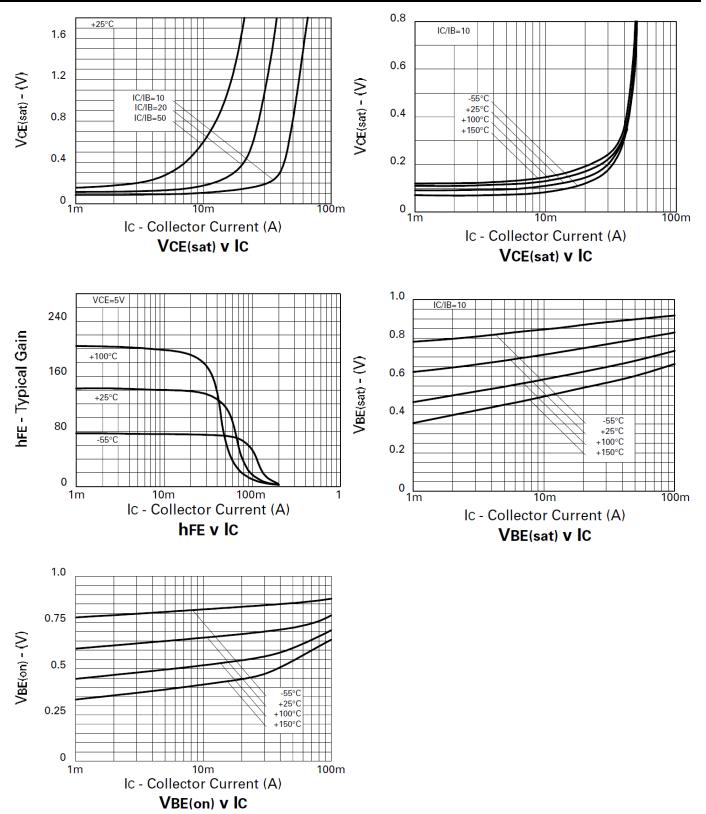
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-500	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-500	_	-	V	$I_{\rm C} = -1 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	-	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	-	-	-100	nA	V _{CB} = -500V
Collector Cut-Off Current	ICES	-	-	-100	nA	V _{CE} = -500V
Emitter Cut-Off Current	I _{EBO}	-	_	-100	nA	V _{EB} = -5.6V
Collector Emitter Seturation Voltage (Note 10)	V _{CE(sat)}	-	-	-200	mV	$I_{\rm C} = -20 {\rm mA}, I_{\rm B} = -2 {\rm mA}$
Collector-Emitter Saturation Voltage (Note 10)		-	-	-500	IIIV	$I_{\rm C} = -50 {\rm mA}, I_{\rm B} = -10 {\rm mA}$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	-	-900	mV	I _C = -50mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	-	-900	mV	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V}$
	h _{FE}	100	-	300		$I_{C} = -1mA, V_{CE} = -10V$
DC Current Gain (Note 10)		80	_	300	-	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V}$
		_	15	-		$I_{C} = -100 \text{mA}, V_{CE} = -10 \text{V}$
Current Gain-Bandwidth Product	fT	60	-	_	MHz	$V_{CE} = -20V$, $I_C = -10mA$ f = 50MHz
Turn-On Time	t _{on}	_	110	_	ns	V _{CC} = -100V, I _C = -50mA
Turn-Off Time	t _{off}	-	1.5	-	μs	$I_{B1} = -5mA, I_{B2} = 10mA$
Output Capacitance	C _{obo}	-	_	8	pF	V _{CB} = -20V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%.





Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

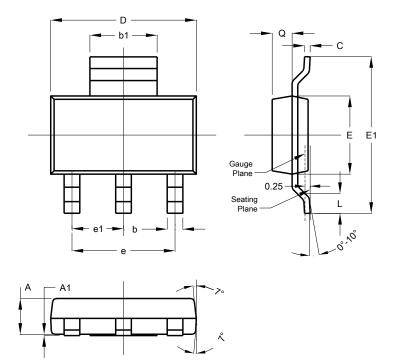






Package Outline Dimensions

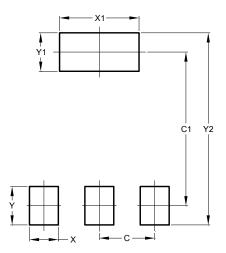
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
ш	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
e	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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